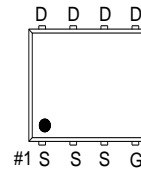
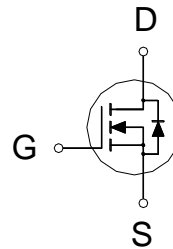




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	8mΩ	39A



G. GATE
D. DRAIN
S. SOURCE

Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.
- 100% UIS and Rg Tested.

Applications

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	I_D	39	A
	$T_C = 100\text{ °C}$		25	
Pulsed Drain Current ¹		I_{DM}	80	
Continuous Drain Current ⁴	$T_A = 25\text{ °C}$	I_D	13	
	$T_A = 70\text{ °C}$		10	
Avalanche Current		I_{AS}	19	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	18	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	22	W
	$T_C = 100\text{ °C}$		9	
Power Dissipation ³	$T_A = 25\text{ °C}$	P_D	2.5	W
	$T_A = 70\text{ °C}$		1.6	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		50	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		89	
Junction-to-Case	Steady-State	$R_{\theta JC}$		5.5	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.

³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.65	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
		$V_{DS} = 30V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ⁴	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 13A$		8.7	12	m Ω
		$V_{GS} = 10V, I_D = 13A$		5.6	8	
Forward Transconductance ⁴	g_{fs}	$V_{DS} = 5V, I_D = 13A$		42		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		577		pF
Output Capacitance	C_{oss}			304		
Reverse Transfer Capacitance	C_{rss}			26		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.6		Ω
Total Gate Charge ⁵	Q_g	$V_{DS} = 15V, V_{GS} = 10V, I_D = 13A$	$V_{GS} = 10V$	10		nC
			$V_{GS} = 4.5V$	5.4		
Gate-Source Charge ⁵	Q_{gs}		1.4			
Gate-Drain Charge ⁵	Q_{gd}		2.4			
Turn-On Delay Time ⁵	$t_{d(on)}$		8		nS	
Rise Time ⁵	t_r	60				
Turn-Off Delay Time ⁵	$t_{d(off)}$	18				
Fall Time ⁵	t_f	76				

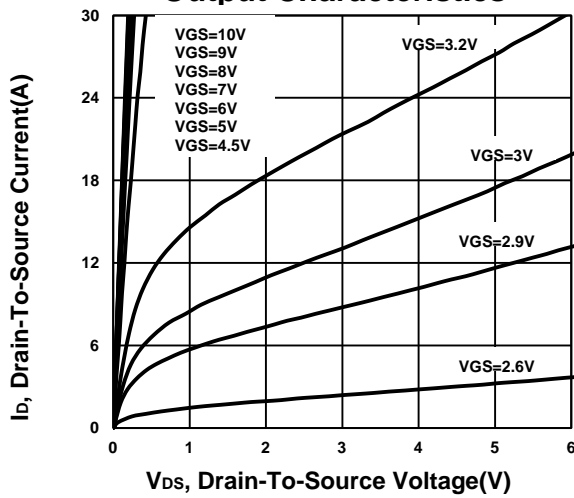
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)

Continuous Current	I _S			18	A
Forward Voltage ⁴	V _{SD}	I _F = 13A, V _{GS} = 0V		1.2	V
Reverse Recovery Time	t _{rr}	I _F = 13A, di _F /dt = 100A / μS		15	nS
Reverse Recovery Charge	Q _{rr}			4.7	nC

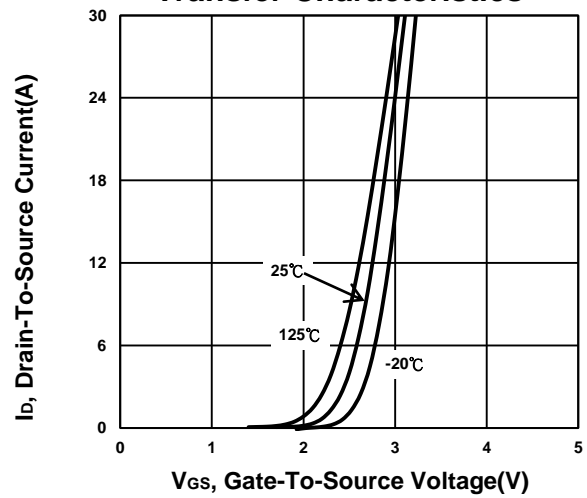
⁴Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

⁵Independent of operating temperature.

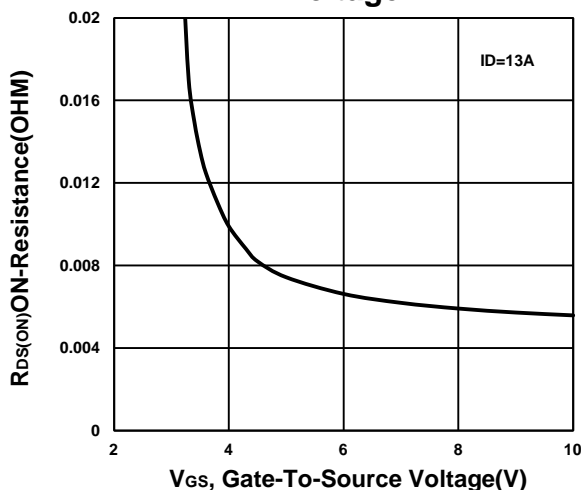
Output Characteristics



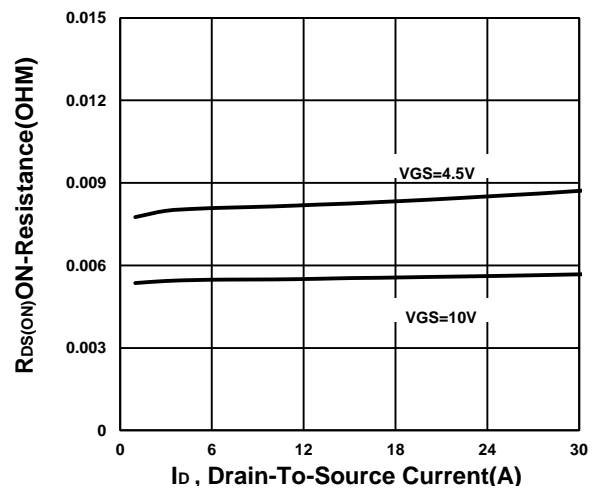
Transfer Characteristics



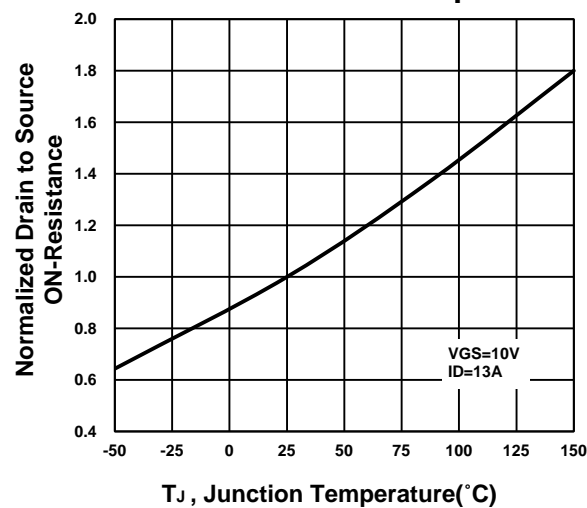
On-Resistance VS Gate-To-Source Voltage



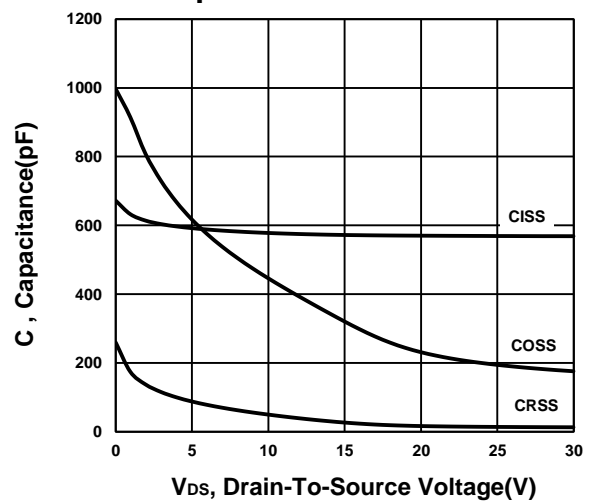
On-Resistance VS Drain Current



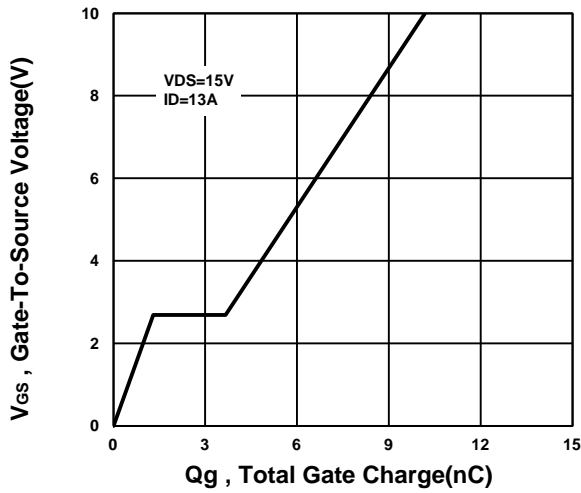
On-Resistance VS Temperature



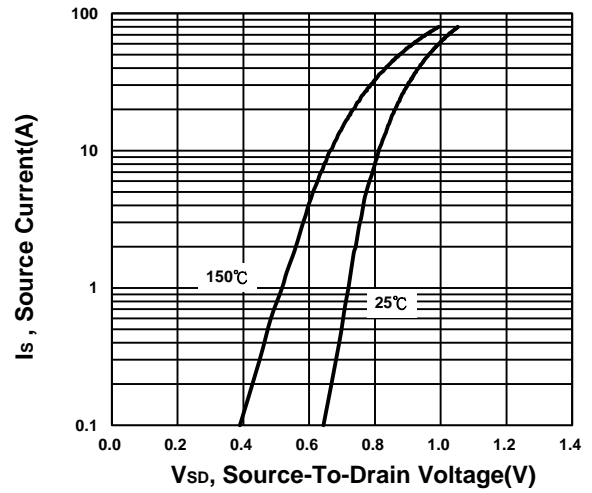
Capacitance Characteristic



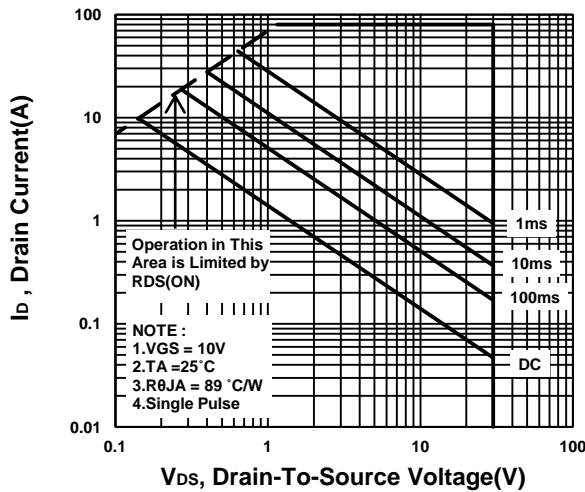
Gate charge Characteristics



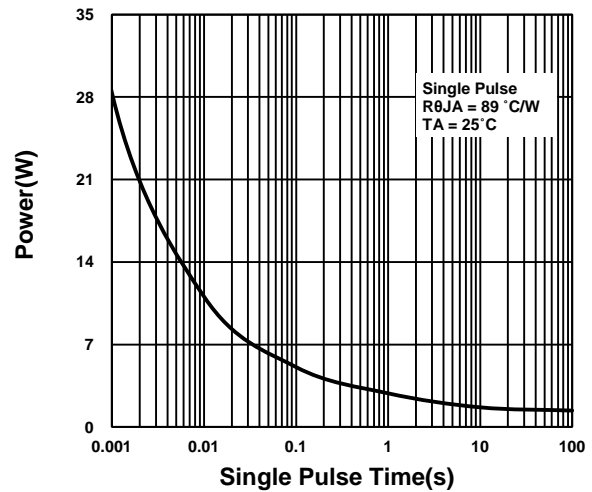
Source-Drain Diode Forward Voltage



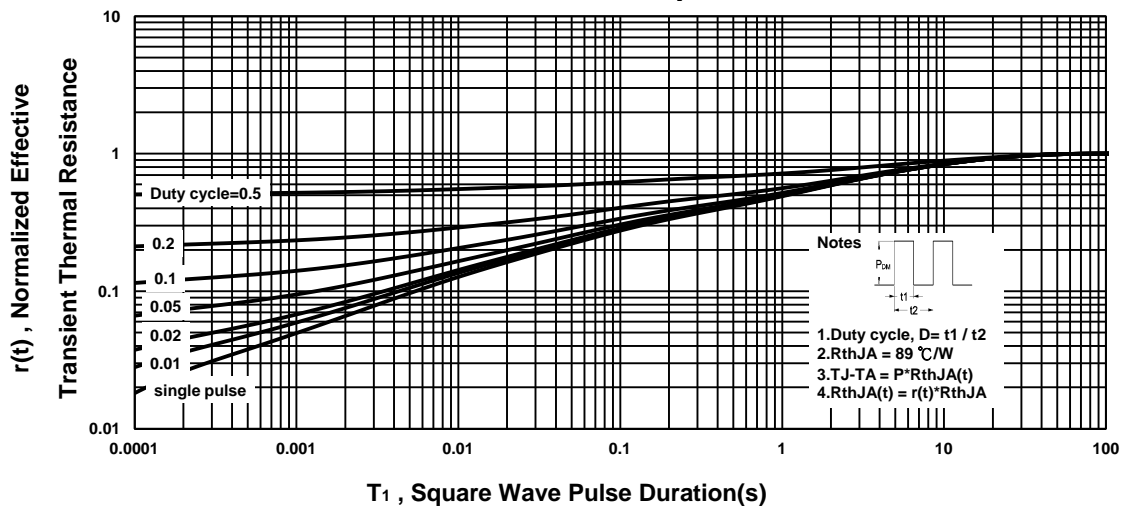
Safe Operating Area



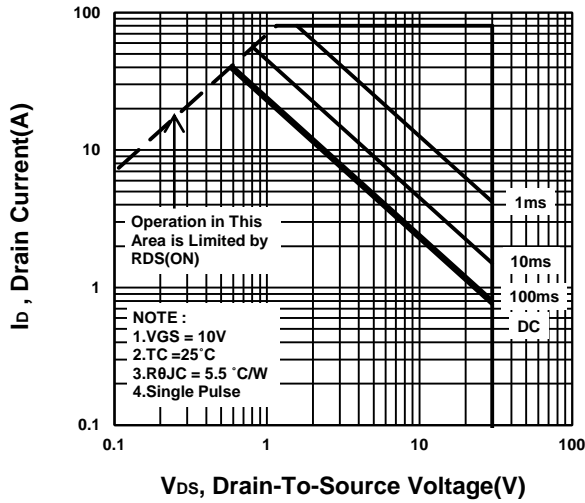
Single Pulse Maximum Power Dissipation



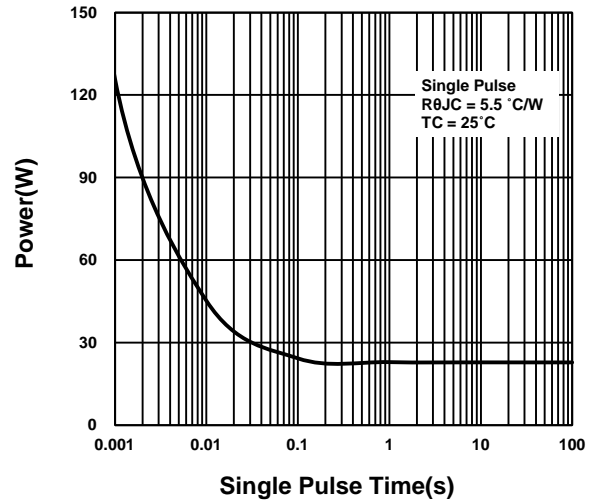
Transient Thermal Response Curve



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

